



Laboratoire Lasers Plasmas et Procédés Photoniques  
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# RECHERCHES AU LABORATOIRE LP3 SUR LES APPLICATIONS DES LASERS AU PHOTOVOLTAÏQUE

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# Collaborations





**Nanosecond lasers (excimer and Nd:YAG) :**

*Wavelength* : 193nm, 248nm, 308nm, 532nm, 1064nm

*Energy* : up to 2J

*Average power* : up to 1kW

*Pulse duration* : from 6 to 80ns

**Picosecond lasers (Nd:YAG) :**

*Wavelength* : 266nm, 355nm, 532nm, 1064nm

*Energy* : from 120mJ to 30mJ

*Repetition rate* : 10Hz

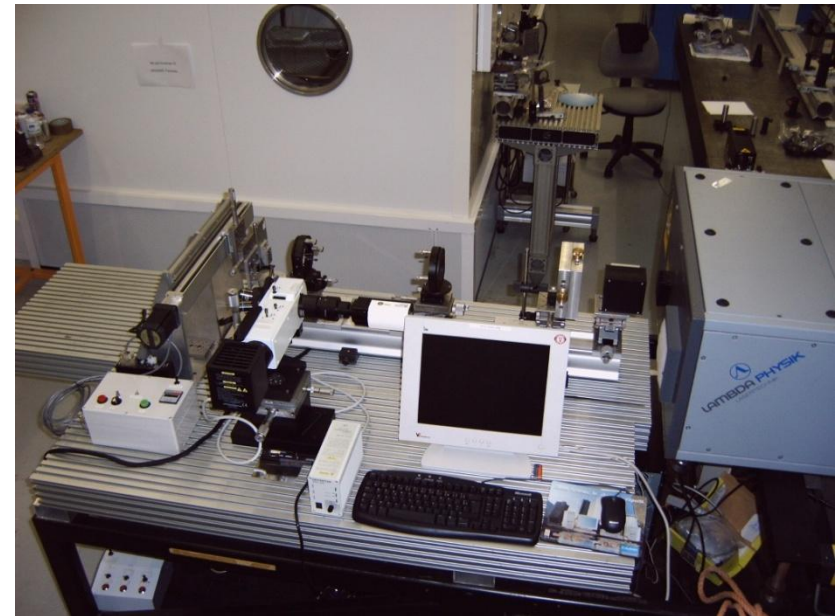
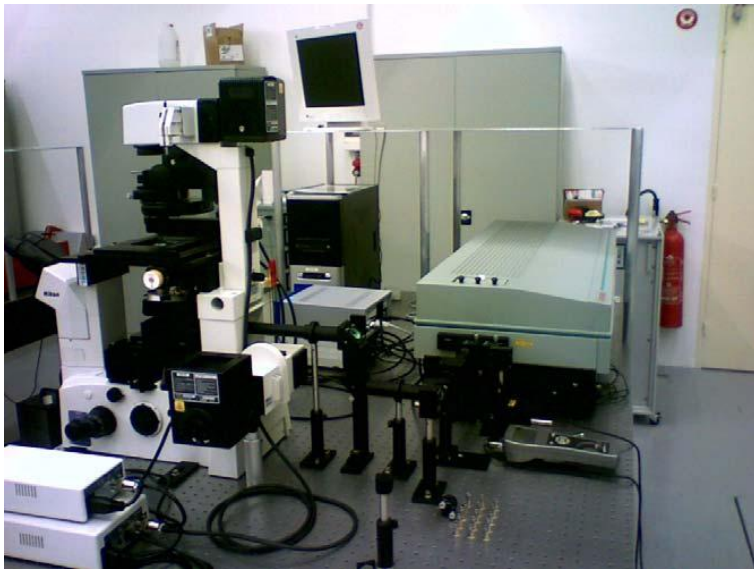
*Pulse duration* : 50ps

**Femtosecond lasers (TiSa and Ytterbium) :**

TiSa from Spectra Physics : 800nm, 1mJ, 100fs, 1kHz

Ytterbium from Amplitude Systems : 1025nm, 450fs, 100μJ@10kHz, 200μJ@1kHz

- Interaction cell : control of gaz nature and pressure, optical windows for diagnostics, ...
- Fast ICCD cameras (10ns) for imaging
- In situ microscope for sample vizualisation
- Microscope for laser beam coupling and vizualisation
- spin coating, thermal evaporator
- Clean room class 1 for laser treatment
- AFM, MEB
- etc...





## FP7 - SOLASYS

### Laser Applications for Solar Cell and Solar Module Production

**High speed Laser micro ablation**

**Laser isolation**

**Laser texturization (black silicon)**

**High speed laser drilling for back-side contact cells**

**Laser joining for cell interconnection**

**Laser selective emitter doping**

Ag  
SiNx  
AlBSF

$\eta +0.5\%$

# MRS BULLETIN

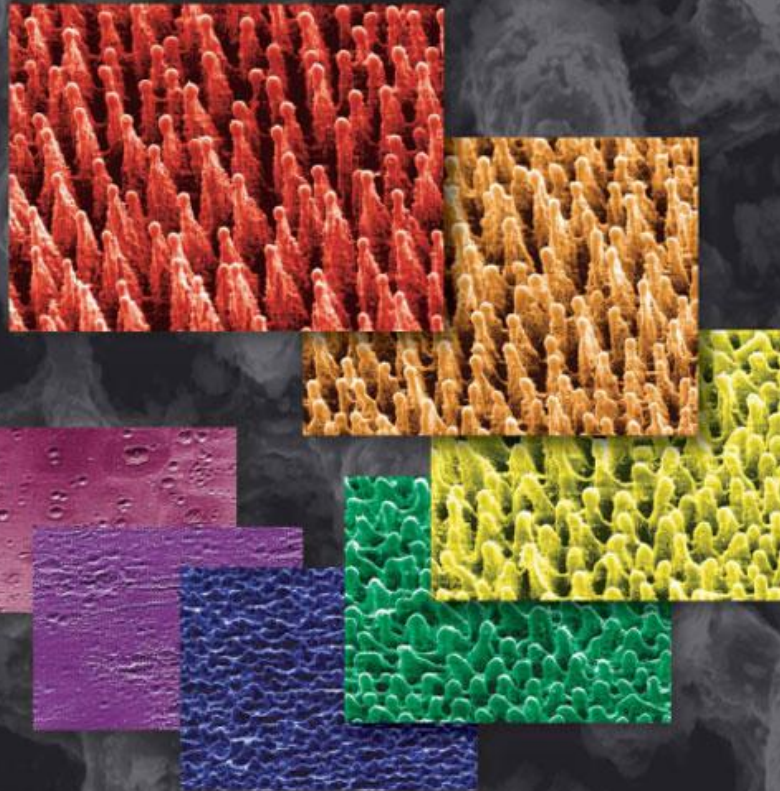
August 2006, Volume 31, No. 8

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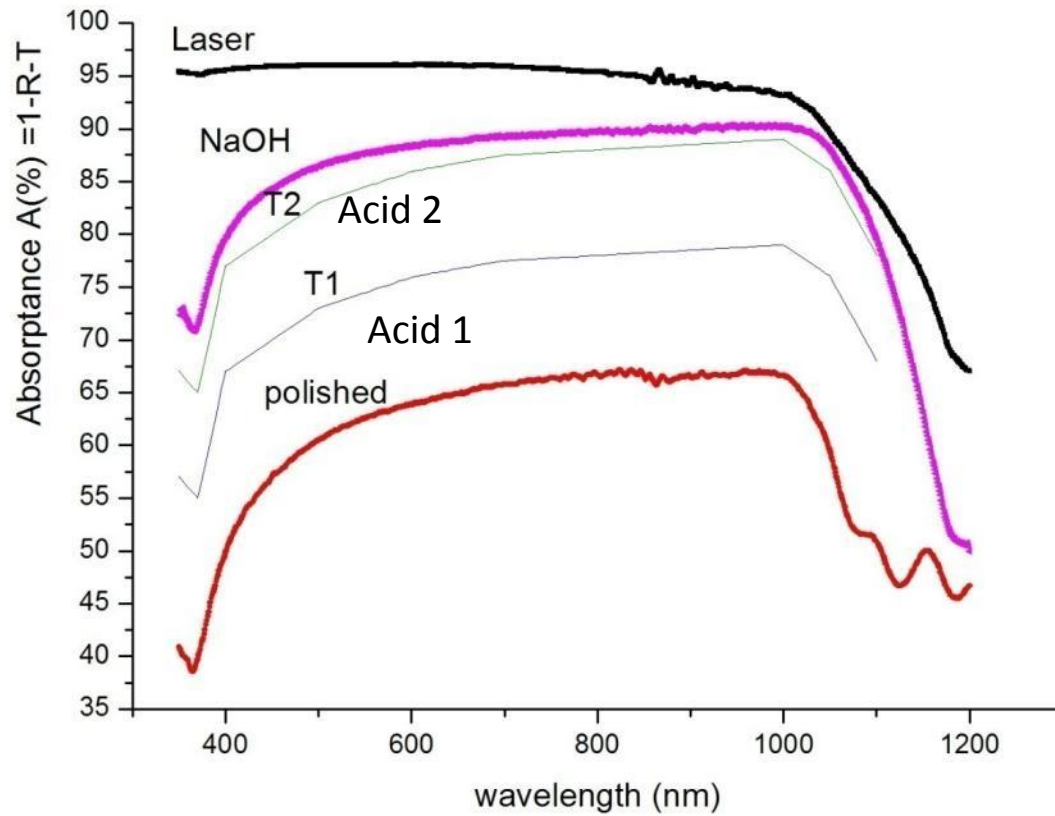
A Publication of the Materials Research Society

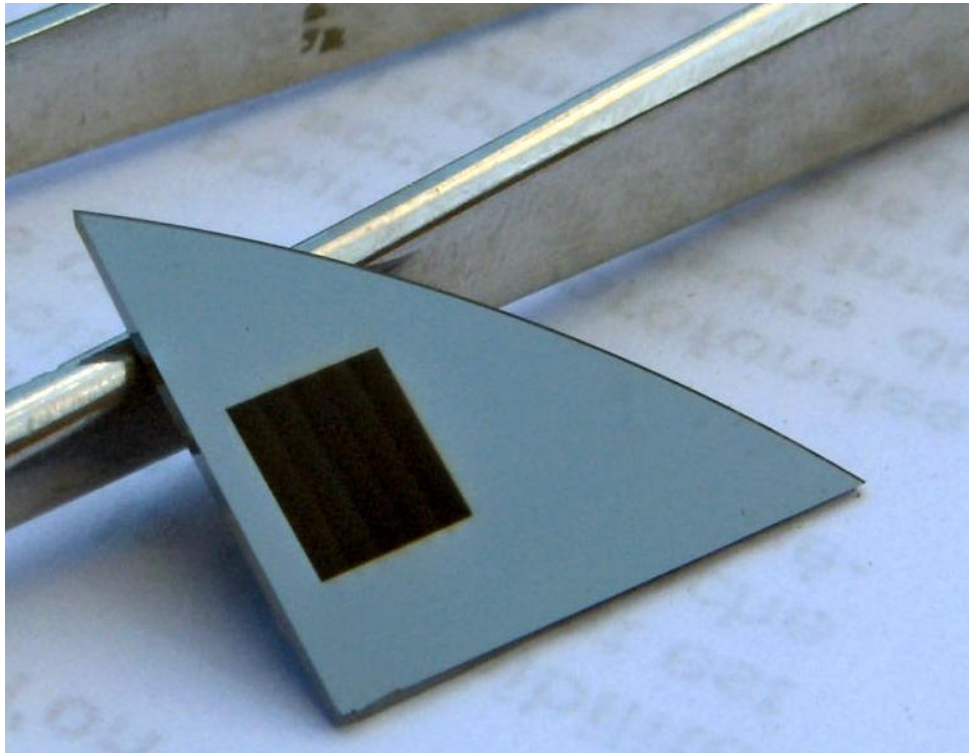


## Ultrafast Lasers in Materials Research



# Absorptance for different texturizations





Optical : up to 97 % optical absorption (mono Si or multi Si)  
Electrical: up to +50-60 % increase of the photocurrent





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